



N-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}	30V
I_D	3.6A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	33mohm
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	48mohm
100% V_{DS} Tested	

General Description

Trench Power MV MOSFET technology
High Power and current handing capability
Moisture Sensitivity Level 1
Epoxy Meets UL 94 V-0 Flammability Rating
Halogen Free

Applications

PWM application
Load switch

Absolute Maximum Ratings ($T_A=25$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
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YJL2304A

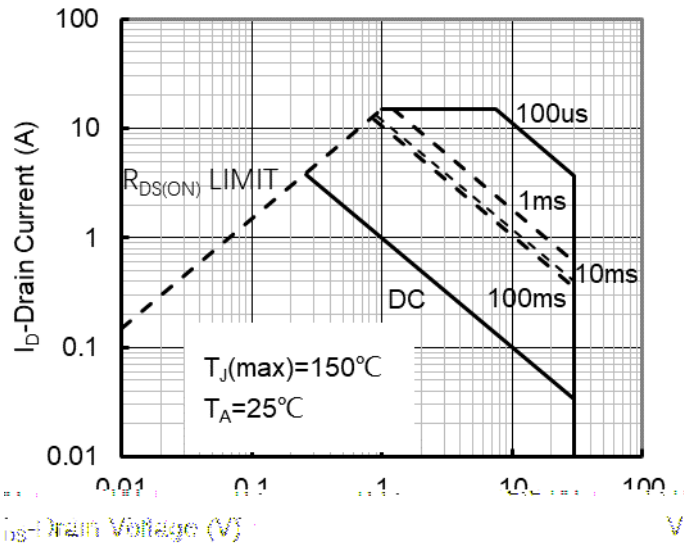


Figure7. Safe Operation Area

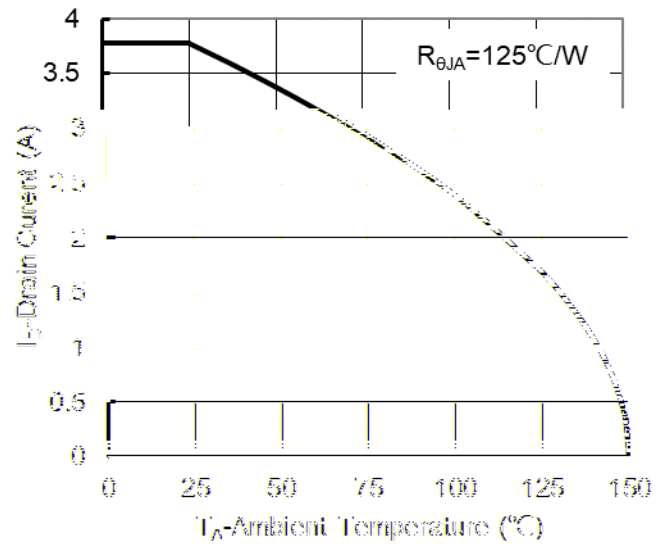


Figure8. Maximum Continuous Drain Current vs Ambient Temperature

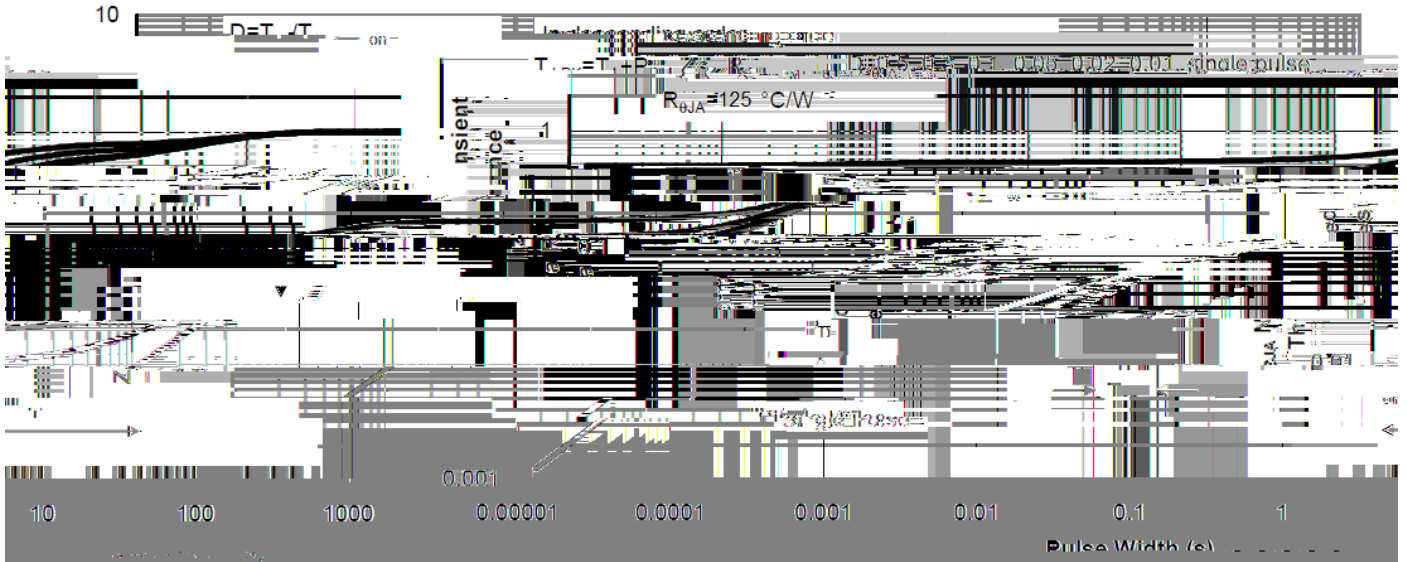
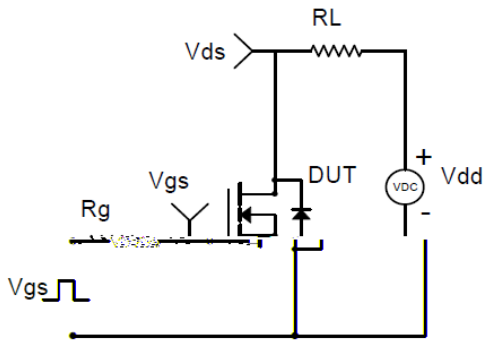
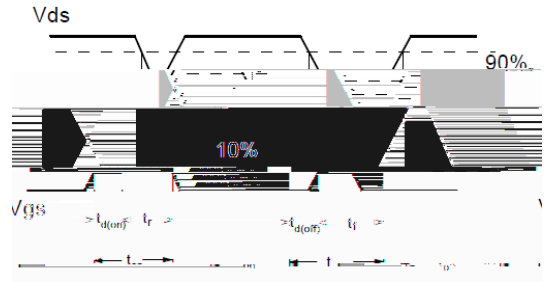


Figure9. Normalized Maximum Transient Thermal Impedance

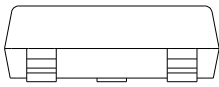
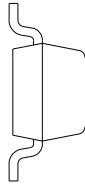
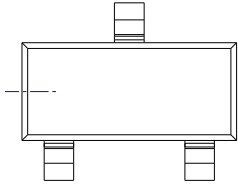


Resistive





SOT-23 Package information



UNIT mm



Disclaimer

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The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of which would directly endanger human life (such as medical instruments, etc.).